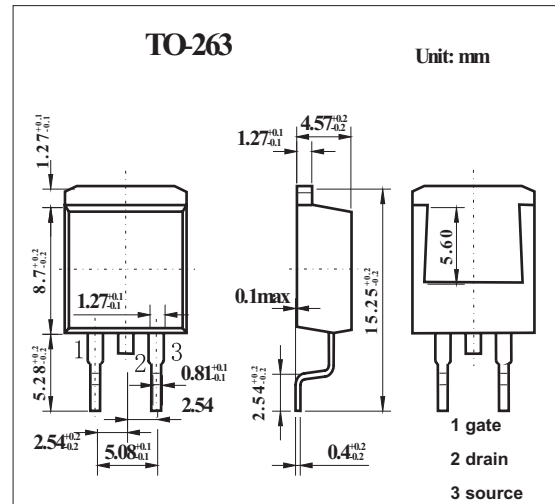
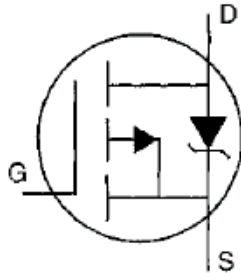


HEXFET[®] Power MOSFET

KRF9610S

■ Features

- Surface Mount
- Available in Tape & Reel
- Dynamic dv/dt Rating
- P-Channel
- Fast Switching
- Simple Drive Requirements



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Continuous Drain Current, V _{GS} @ -10V, T _c = 25°C	I _D	-1.8	A
Continuous Drain Current, V _{GS} @ -10V, T _c = 100°C	I _D	-1	
Pulsed Drain Current*1	I _{DM}	-7	
Power Dissipation T _c = 25°C	P _D	20	W
Power Dissipation (PCB Mount) Ta = 25°C		3	
Linear Derating Factor		0.16	W/°C
Linear Derating Factor (PCB Mount) *3		0.025	
Gate-to-Source Voltage	V _{GS}	±20	V
Inductive Current, .Clamp	I _{LM}	-7	A
Peak Diode Recovery dv/dt *2	dv/dt	-5	V/ns
Operating Junction and Storage Temperature Range	T _J , T _{STG}	-55 to + 150	°C
Junction-to-Case	R _{θJC}	6.4	°C/W
Junction-to-Ambient (PCB Mounted) *3	R _{θJA}	40	°C/W
Junction-to-Ambient	R _{θJA}	62	°C/W

*1 Repetitive rating; pulse width limited by max. junction temperature.

*2 I_{SD} ≤ -1.8A, di/dt ≤ 70A/μs, V_{DD} ≤ V(BR)DSS, T_J ≤ 150°C

*3 When mounted on 1" square PCB

KRF9610S

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = -250 \mu A$	-200			V
Breakdown Voltage Temp. Coefficient	$\Delta V_{(BR)DSS} / \Delta T_J$	$I_D = -1mA, \text{Reference to } 25^\circ C$		-0.23		V/°C
Static Drain-to-Source On-Resistance	$R_{DS(on)}$	$V_{GS} = -10V, I_D = -0.9A^{*1}$			3.0	Ω
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250 \mu A$	-2.0		-4.0	V
Forward Transconductance	g_{fs}	$V_{DS} = -50V, I_D = -0.90A^{*1}$	0.90			S
Drain-to-Source Leakage Current	I_{DSS}	$V_{DS} = -200V, V_{GS} = 0V$			-100	μA
		$V_{DS} = -160V, V_{GS} = 0V, T_J = 125^\circ C$			-500	
Gate-to-Source Forward Leakage	I_{GSS}	$V_{GS} = 20V$			-100	nA
Gate-to-Source Reverse Leakage		$V_{GS} = -20V$			100	
Total Gate Charge	Q_g	$I_D = -3.5A$			11	nC
Gate-to-Source Charge	Q_{gs}	$V_{DS} = -160V$			7.0	
Gate-to-Drain ("Miller") Charge	Q_{gd}	$V_{GS} = -10V, ^{*1}$			4.0	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -100V$		8.0		ns
Rise Time	t_r	$I_D = -0.90A$		15		
Turn-Off Delay Time	$t_{d(off)}$	$R_G = 50 \Omega$		10		
Fall Time	t_f	$R_D = 110 \Omega^{*1}$		8.0		
Internal Drain Inductance	L_D	Between lead, 6 mm (0.25in.) from package and center of die contact		4.5		nH
Internal Source Inductance	L_S			7.5		
Input Capacitance	C_{iss}	$V_{GS} = 0V$		170		pF
Output Capacitance	C_{oss}	$V_{DS} = -25V$		50		
Reverse Transfer Capacitance	C_{rss}	$f = 1.0MHz$		15		
Continuous Source Current (Body Diode)	I_S	MOSFET symbol showing the integral reverse p-n junction diode.			-1.8	A
Pulsed Source Current (Body Diode) *2	I_{SM}				-7.0	
Diode Forward Voltage	V_{SD}	$T_J = 25^\circ C, I_S = -1.8A, V_{GS} = 0V^{*1}$			-5.8	V
Reverse Recovery Time	t_{rr}	$T_J = 25^\circ C, I_F = -1.8A$		240	360	ns
Reverse Recovery Charge	Q_{rr}	$di/dt = 100A/\mu s^{*1}$		1.7	2.69	μC
Forward Turn-On Time	t_{on}	Intrinsic turn-on time is negligible (turn-on is dominated by $L_S + L_D$)				

*1 Pulse width $\leq 300 \mu s$; duty cycle $\leq 2\%$.

*2 Repetitive rating; pulse width limited by max